

NRVTS2H60ESF, NRVTSM260EV2

Very Low Forward Voltage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 11.7 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds
- MSL 1

Typical Applications

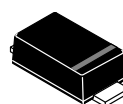
- Switching Power Supplies including Compact Adapters and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation



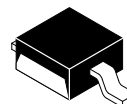
ON Semiconductor®

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TRENCH SCHOTTKY RECTIFIER 2.0 AMPERES 60 VOLTS

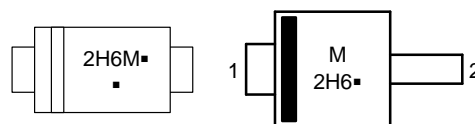


SOD-123FL
CASE 498



POWERMITE
CASE 457

MARKING DIAGRAMS



2H6 = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NRVTS2H60ESFT1G	SOD-123FL (Pb-Free)	3,000 / Tape & Reel
NRVTS2H60ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel
NRVTSM260EV2T1G	Powermite (Pb-Free)	3,000 / Tape & Reel
NRVTSM260EV2T3G	Powermite (Pb-Free)	12,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NRVTS2H60ESF, NRVTSM260EV2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current ($T_L = 125^\circ\text{C}$)	I_O	2.0	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, $T_L = 139^\circ\text{C}$)	I_{FRM}	4.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	-65 to +175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
SOD-123FL			
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	24.4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	85	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	330	$^\circ\text{C/W}$

POWERMITE

Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	8.6	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	237	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 1.0\text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 2.0\text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 1.0\text{ A}, T_J = 125^\circ\text{C}$) ($I_F = 2.0\text{ A}, T_J = 125^\circ\text{C}$)	V_F	0.55 0.65 0.47 0.58	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	12 3	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
- Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
- Pulse Test: Pulse Width $\leq 380\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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TYPICAL CHARACTERISTICS

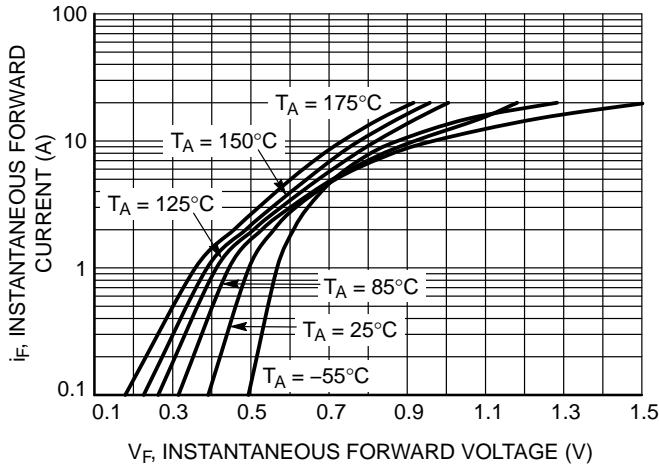


Figure 1. Typical Instantaneous Forward Characteristics

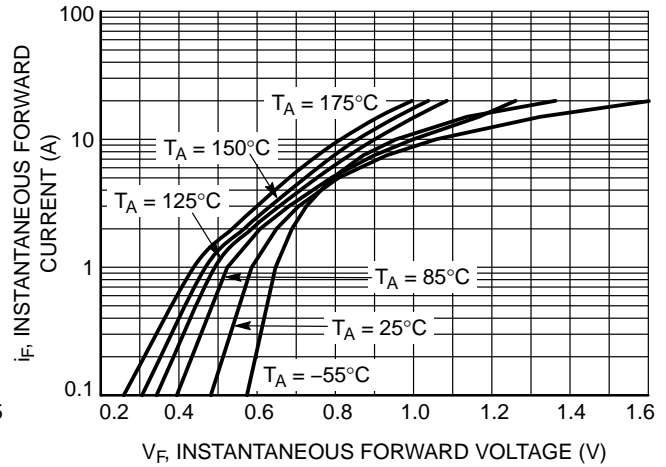


Figure 2. Maximum Instantaneous Forward Characteristics

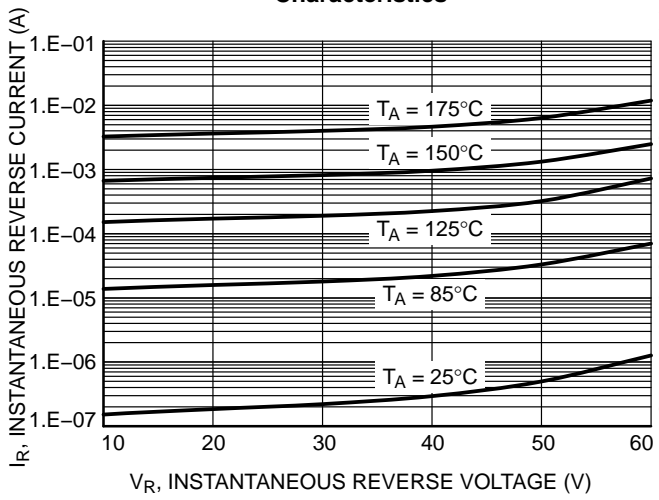


Figure 3. Typical Reverse Characteristics

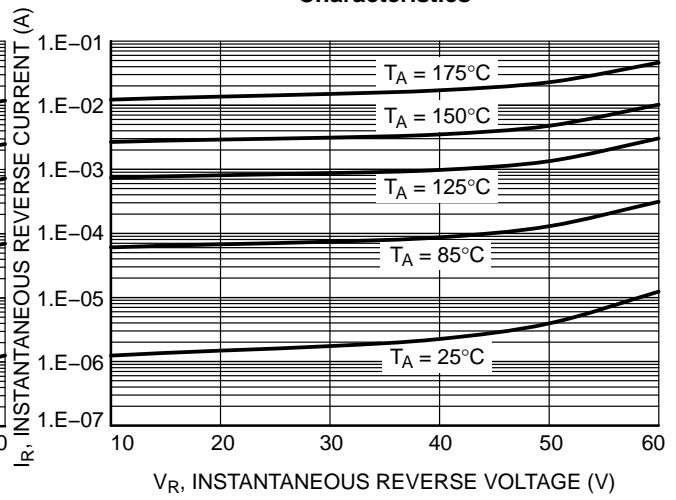


Figure 4. Maximum Reverse Characteristics

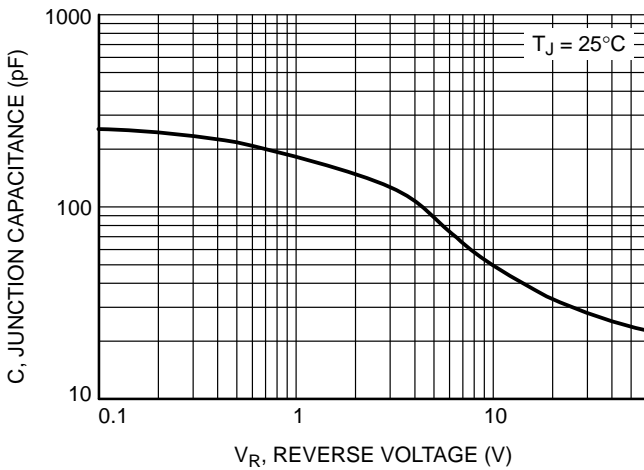


Figure 5. Typical Junction Capacitance

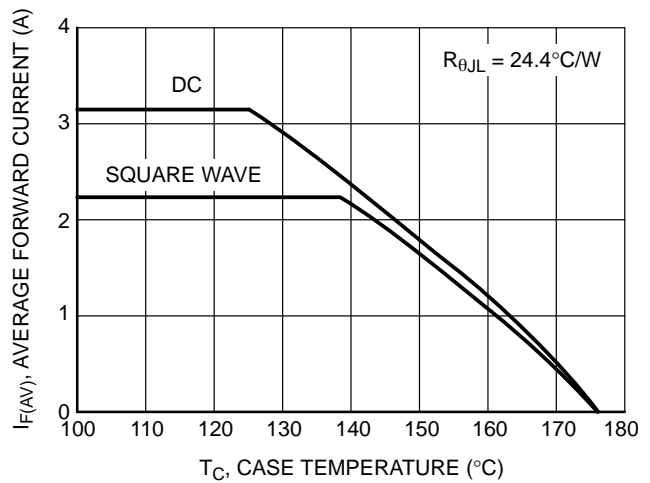


Figure 6. Current Derating

NRVTS2H60ESF, NRVTSM260EV2

TYPICAL CHARACTERISTICS

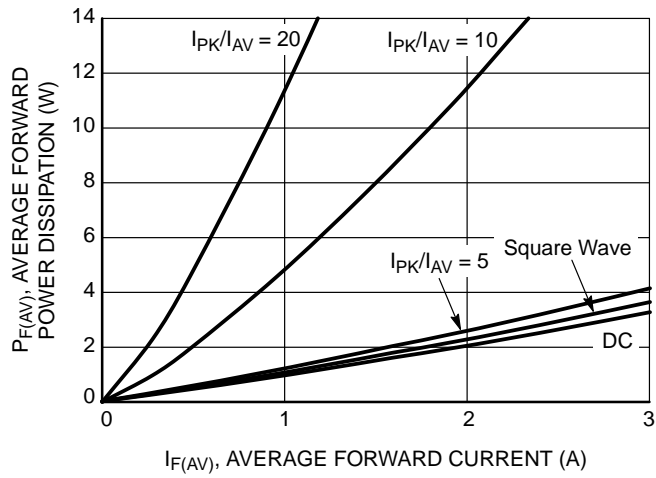


Figure 7. Forward Power Dissipation

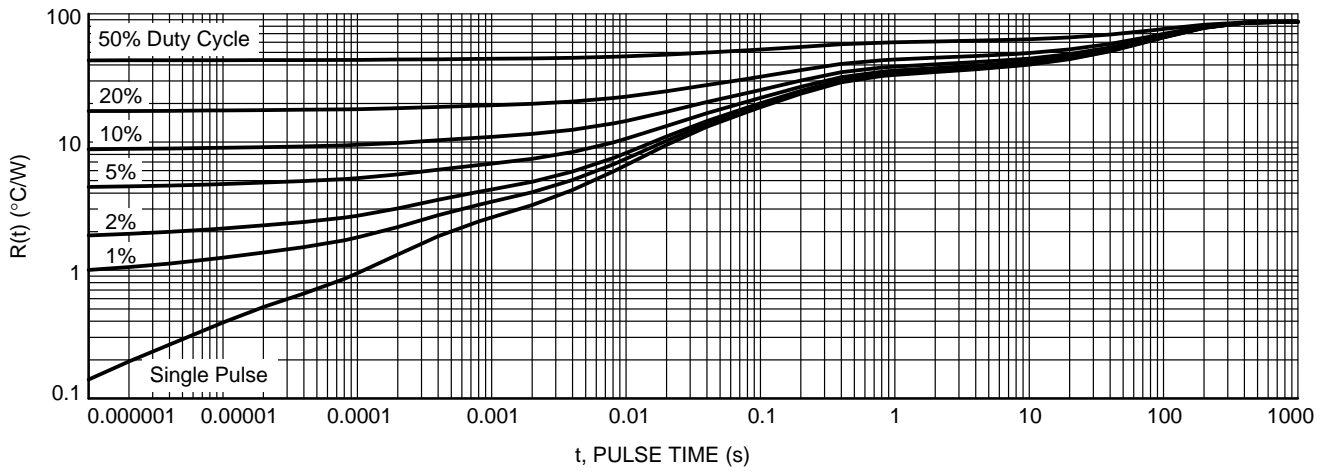
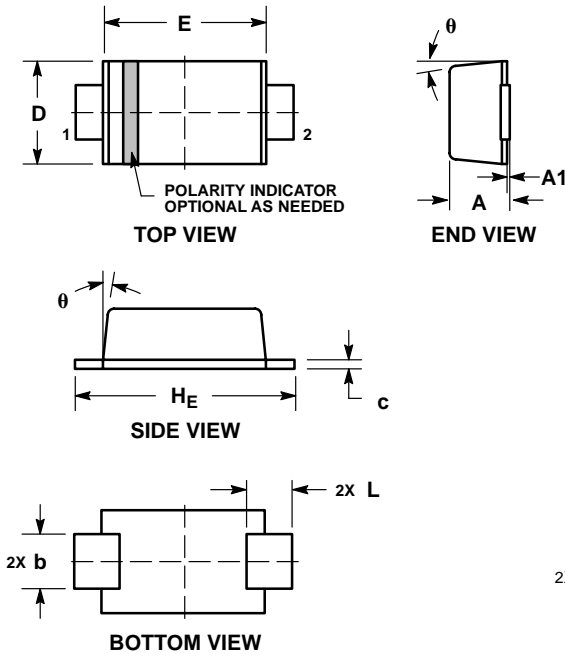


Figure 8. Thermal Characteristics

NRVTS2H60ESF, NRVTSM260EV2

PACKAGE DIMENSIONS

SOD-123FL
CASE 498
ISSUE D

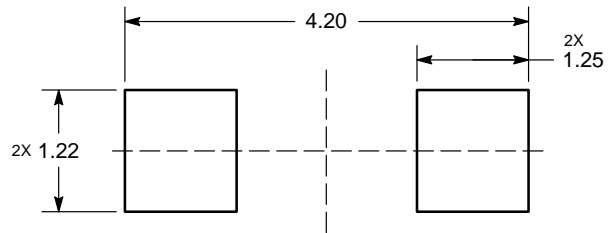


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH.
4. DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	0.95	0.98	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.70	0.90	1.10	0.028	0.035	0.043
c	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
E	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
H _E	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	-	8°	0°	-	8°

RECOMMENDED SOLDERING FOOTPRINT*



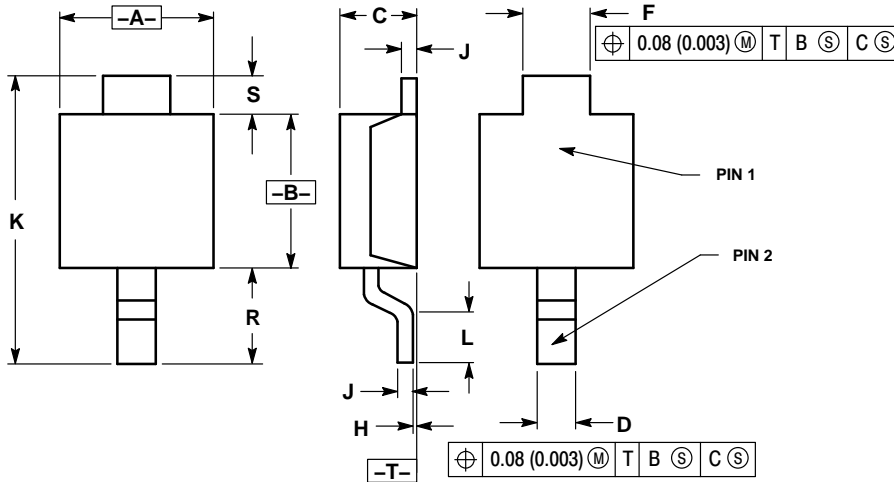
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NRVTS2H60ESF, NRVTSM260EV2

PACKAGE DIMENSIONS

POWERMITE
CASE 457-04
ISSUE F

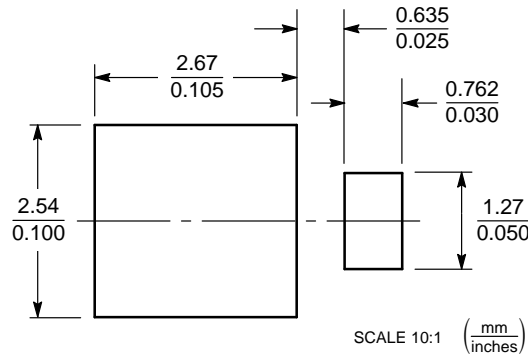


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.75	2.05	0.069	0.081
B	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
H	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50	REF	0.019	REF

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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